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501.35437VX1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: YOSHIDA et al.
Serial No.: 09/416,959
Filed: October 13, 1999
For: SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE
AND PROCESS FOR MANUFACTURING THE SAME
Group: 2812
Examiner: J. Hack

SUPPLEMENTAL PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

January 20, 2000

Sir:

Prior to examination, please amend the above-identified application as follows:

IN THE CLAIMS

Please add the following new claims:

B1
-- 9. A method of manufacturing a semiconductor integrated circuit device comprising the steps of:

(a) forming a MISFET on main surface of a semiconductor substrate,

(b) forming a first insulating film over the MISFET,

(c) forming a first conductor film on the first insulating film,

(d) forming a second insulating film over the first conductor film,

(e) forming a first electrode for a capacitor cell on the second insulating film,

TO EXAMINE
JAN 20 2000
JPO